## UNIVERSITI SAINS MALAYSIA

First Semester Examination Academic Session 2006/2007

October/November 2006

## **EEE 510 – ADVANCED ANALOGUE CIRCUIT DESIGN**

Duration: 3 hours

Please check that this examination paper consists of SEVEN pages of printed material and ONE pages Appendix before you begin the examination.

This paper contains SIX questions.

Instructions: Answer FIVE (5) questions.

Answer to any question must start on a new page.

Distribution of marks for each question is given accordingly

All questions must be answered in English.

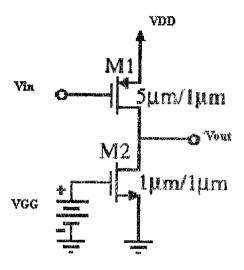


Figure 2 : Common source amplifier

- 2. A CMOS amplifier is shown in Figure 2. Assume M1 and M2 operate in the saturation region.
  - (a) What value of V<sub>GG</sub> gives 100µA through M1 and M2? (6 marks)
  - (b) What is the DC value of input voltage V<sub>in</sub>? (6 marks)
  - (c) What is the small signal voltage gain, V<sub>out</sub>/V<sub>in</sub>? (8 marks)
- 3. (a) Explain the advantages and disadvantages of differential amplifier over single common source amplifier.

(10 marks)

(b) Based on Figure 3, calculate output resistance,  $R_{out}$  and voltage gain when  $I_{ss}$ =10 $\mu A$ .

(10 marks)

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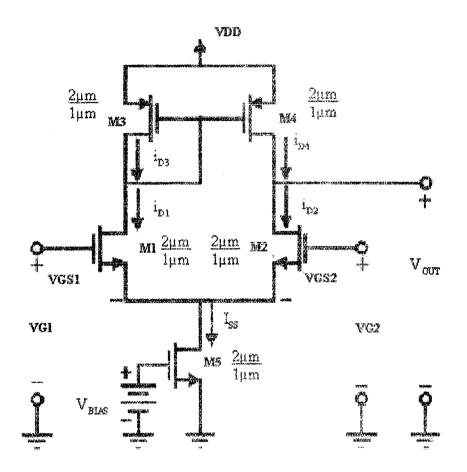


Figure 3: Differential amplifier with single-ended output

(b) Refer to Figure 6. Sketch  $I_X$  versus  $V_X$  as  $V_X$  varies for 0 to  $V_{DD}$ . (10 marks)

## Miller CMOS OTA

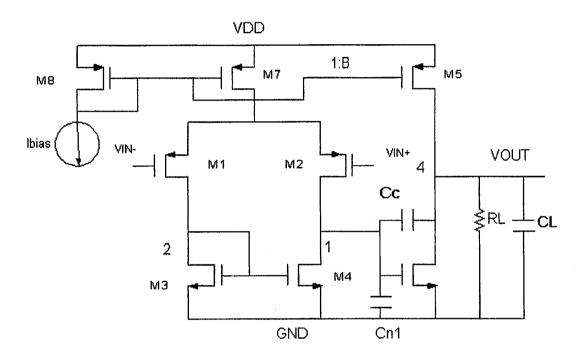


Figure 7

6. Derive the expression for

(a) Bandwidth (5 marks)(b) Gain Bandwidth (10 marks)(c) Non Dominant Pole (5 marks)

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**APPENDIX** 

Model Parameters for a Typical CMOS Bulk Process Suitable for Hand Calculations Using the Simple Model with Values Based on a 0.8  $\mu$ m Silicon-Gate Bulk CMOS n-Well Process

Parameter Symbol	Parameter Description	Typical Parameter Value		
		n-Channel	p-Channel	Units
V <sub>70</sub>	Threshold voltage $(V_{BS} = 0)$	0.7 ± 0.15	-0.7 ± 0.15	٧
K'	Transconductance parameter (in saturation)	110.0 ± 10%	50.0 ± 10%	μA/V²
γ	Bulk threshold parameter	0.4	0.57	V <sup>1/2</sup>
λ	Channel length modulation parameter	$0.04 (L = 1 \mu m)$ $0.01 (L = 2 \mu m)$	$0.05 (L = 1 \mu m)$ $0.01 (L = 2 \mu m)$	V-1
$2 \phi_F $	Surface potential at strong inversion	0.7	0.8	<b>V</b>